

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	"6497801".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 10:19
S2	2	"6261433".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 10:22
S3	20	(Landau near2 Uziel).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 10:22
S4	48	("3649509" "3727620" "3770598" "4027686" "4092176" "4110176" "4113492" "4315059" "4326940" "4336114" "4376685" "4405416" "4428815" "4435266" "4489740" "4510176" "4518678" "4519846" "4693805" "4732785" "4789445" "5039381" "5055425" "5092975" "5155336" "5162260" "5222310" "5224504" "5230743" "5252807" "5256274" "5259407" "5290361" "5316974" "5328589" "5349978" "5368711" "5377708" "5429733" "5447615" "5516412" "5608943" "5625170" "5651865" "5705223" "5718813" "5723028").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 08:58
S5	1	"6391166".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 09:34
S6	86456	(segment\$3 or plurality) near3 (anode or electrode or cathode)	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 09:55

S7	17997	(anode or cathode or electrode) with (independent or different or own or individual) near3 (power or voltage or current)	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 10:29
S13	6941	S6 and S7	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 09:55
S14	2245	S13 and (semiconductor or wafer)	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 09:55
S15	406	S14 and (anode or cathode or electrode) near5 (ring or concentric or coaxial or annular)	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 10:26
S17	318	S15 and (plating or polishing or etching or deposit\$4)	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 10:31
S18	92	S17 and ("204"/\$.ccls. or "205"/\$.ccls.)	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 10:23
S20	20461	(segment\$3 or plurality) near3 (anode or electrode or cathode)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 10:23
S21	3937	(anode or cathode or electrode) with (independent or different or own or individual) near3 (power or voltage or current)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 10:23
S22	3316	S20 and (semiconductor or wafer)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 10:26
S23	0	S22 and (plating or polishing or etching or deposit\$4)	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 10:26
S25	0	S22 and (electroplating or (electro adj plating))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 10:25
S27	50	S22 and (anode or cathode or electrode) near5 (ring or concentric or coaxial or annular)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/10 10:27
S28	27929	S6 and (semiconductor or wafer)	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 10:29
S29	2538	S28 and (anode or cathode or electrode) near5 (ring or concentric or coaxial or annular)	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 10:29
S30	406	S29 and (anode or cathode or electrode) with (independent or different or own or individual) near3 (power or voltage or current)	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 10:30

S31	318	S30 and (plating or polishing or etching or deposit\$4)	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 10:31
S32	109	(204/230.7).ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 10:32
S33	15	S32 and (semiconductor or wafer)	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 10:35
S34	1167	"204"/\$.ccls. and (semiconductor or wafer) and (auxiliary or second\$4) adj (electrode or anode or cathode)	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 11:24
S35	281	S34 and plating	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 12:07
S37	190	S34 and (electroplating or (electro adj plating) or (electrochemical adj plating) or (electrochemical adj processing))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 12:09
S38	54	S37 and auxiliary	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 12:14
S39	1	"3755113".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 12:14
S40	3225	electroplating and ((revers\$4 or chang\$4 or var\$3) near3 current)	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 12:15
S41	677	electroplating and ((revers\$4 or chang\$4 or var\$3) near3 current) and "204"/\$.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 12:16
S42	81	S41 and (semiconductor adj wafer)	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/10 12:16